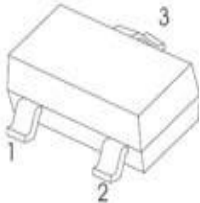
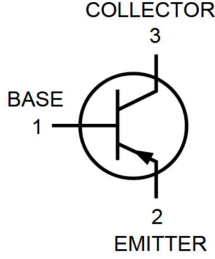


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors																																										
<p style="text-align: center;"><u>SOT-23</u></p>  <div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: left;"> <p>1.BASE 2.EMITTER 3.COLLECTOR</p> </div> <div style="text-align: center;">  </div> </div> <p style="text-align: center;">Marking :2D</p>	<p style="text-align: center;">Features</p> <p style="text-align: center;">※ High Breakdown Voltage</p>																																										
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**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-150	365	-800	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-150	310	-800	V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA, IC=0	-5	11	-30	V
Collector cut-off current	ICBO	VCB=-120 V , IE=0			-0.25	μA
Collector cut-off current	ICEO	VCB=-150V , IE=0			-5	μA
Emitter cut-off current	IEBO	VEB= -4V , IC=0			-0.1	μA
DC current gain	hFE	VCE=-5V, IC= -1mA	60			
	hFE	VCE=-5V, IC= -10mA	100		200	
	hFE	VCE=-5V, IC= -30mA	60			
Collector-emitter saturation voltage	VCE(sat)	IC=-20 mA, IB= -2mA			-0.2	V
Base-emitter saturation voltage	VBE(sat)	IC=-20 mA, IB=- 2mA			-0.9	V
Transition frequency	fT	VCE=-20V, IC= -10mA f=300MHz	50			MHz

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

